

CHAPTER 6

Dielectric Properties of Modified BiFeO₃ Ceramics

In this work, the pure and modified BiFeO₃ (BFO) ceramics (BFO doped with Sb) were synthesized by a solid-state reaction method. Phase formation, microstructure, and dielectric properties were investigated. The samples showed a main phase of rhombohedral BFO. The additive inhibited grain growth, with average grain size decreasing from ~14 μm for pure BFO to 3 μm for the modified BFO samples. The dielectric constant of the modified samples tended to improve with the additive. This improvement can be related to a conduction mechanism in the studied samples.

6.1 Introduction

Multiferroic materials which combine two or more properties of ferroelectric, ferromagnetism, and ferroelasticity are gaining much attention due to their physical properties as well as possibility of practical electronic applications [1-7]. BiFeO₃ (BFO) is one of such materials and has a rhombohedrally distorted simple perovskite structure (ABO₃). It exhibits an antiferromagnetic behavior with a relatively high Neel temperature ($T_N \sim 370$ °C) and ferroelectric behavior with a high Curie temperature ($T_C \sim 830$ °C) [7]. This material has been fabricated in many forms such as single crystal, ceramics and thin films [2-5]. The properties of the fabricated BFO have also been intensively investigated for many years past. However, it should be noted that most BFO ceramics exhibit weak ferroelectric behavior. Furthermore, BFO ceramics also present a large leakage current, which hampered its practical applications. The existence of Fe²⁺ ions and oxygen vacancies has been proposed as a reason for the large leakage current [8]. In order to improve the properties of BFO, several techniques have been proposed such as processing, forming some solid solutions between BFO and other

materials, and doping with some elements [1-2]. In case doping, several elements such as Ba, Ca, Ce, La, Nb, Pb and Mn have been introduced into BFO lattices [1-2, 9-13]. However, electrical properties of BFO doped with Sb have not been investigated, to our knowledge. In the present work, we report for our results showing the effects of Sb doping on the properties of BFO ceramics.

6.2 Experimental

BiFeO₃ doped with Sb was synthesized by a solid-state reaction. Bi₂O₃ (Aldrich, 99.0% purity), Fe₂O₃ (Aldrich, 99.0% purity) and Sb₂O₅ (Aldrich, 99.9% purity) were used as raw metal oxide materials. The raw materials were weighed and then suspended in ethanol and intimately mixed in a ball milling machine for 24 h using zirconia balls as a grinding media. After drying for 24 h, the dried powder was ground, sieved and then calcined at 800 °C for 2 h. The obtained mixture was dried and then uniaxially pressed into a disc shape with a diameter of 1.5 cm. Excess Bi₂O₃ (3 wt. %) was introduced prior to powder calcination to compensate for any Bi₂O₃ that may have been lost from the powder due to volatilization at high temperature. The green discs were sintered at 850 °C with a dwell time of 2 h. The density of the sintered samples was determined by Archimedes' principle. Phase formation of the samples was examined by X-ray diffraction (XRD) technique. For electrical measurement, the sintered samples were polished to obtain parallel surfaces and silver paste electrodes were applied to make an electrode. The dielectric properties of the pellet ceramics were measured using a LCR meter.

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6.3 Results and discussion

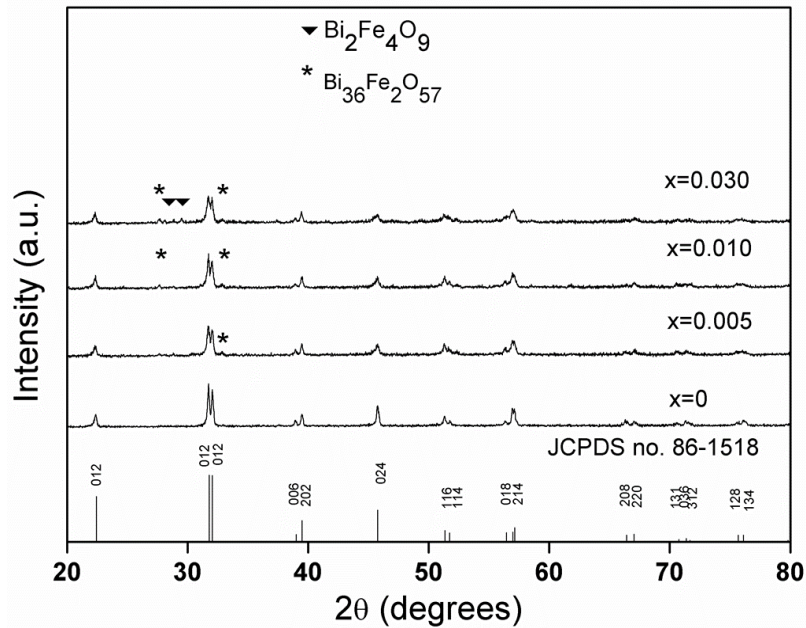


Figure 6.1 displays the XRD patterns of pure and modified BFO ceramics

The XRD result indicates that all main diffraction peaks correspond to a perovskite phase of BFO according to JCPDS file no. 86-1518. In case the unmodified sample, the XRD data shows a pure phase of BFO. The obtained result agrees with the work done by Jim et al. [7]. After doping, however, peaks of impurity phases are presented as seen and indicated in Fig 1. These second phase were identified as Bi₂Fe₄O₉ and Bi₃₆Fe₂O₅₇ according to JCPDS file no. 25-0090 and 42-0181, respectively. The appearance of the impurity phases implies that the additive inhibits the formation of BFO phase. However, the slightly shift in XRD peaks suggests that small amount of Sb ions have entered into the BFO lattices. To check this possibility, energy band gap of the studied ceramics was determined by a UV-Visible spectrometer. The energy band gaps of the samples are listed in Table 6.1. The energy band gap values of the studied samples are in a range of 2.595- 2.579 eV. Plot of absorption spectrum as wavelength of the BiFeO₃ ceramics had showed in Figure 6.6-6.9. The energy band gap range in the present work is close to that reported in previous work [14]. The slightly change in energy band gap therefore confirms the XRD investigation. Furthermore, it should be noted that the XRD peaks

become broader and their intensity decrease with increasing Sb concentration. This implies that the modified BFO ceramics exhibits a lower degree of crystallinity.

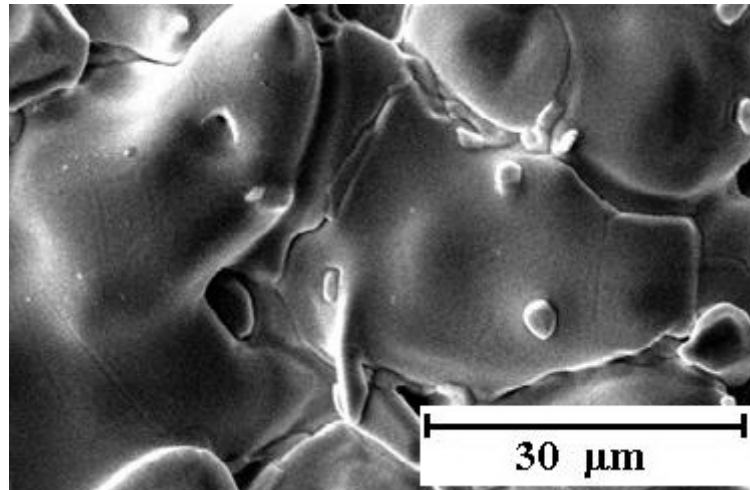


Figure 6.2 SEM micrographs of pure BFO ceramic.

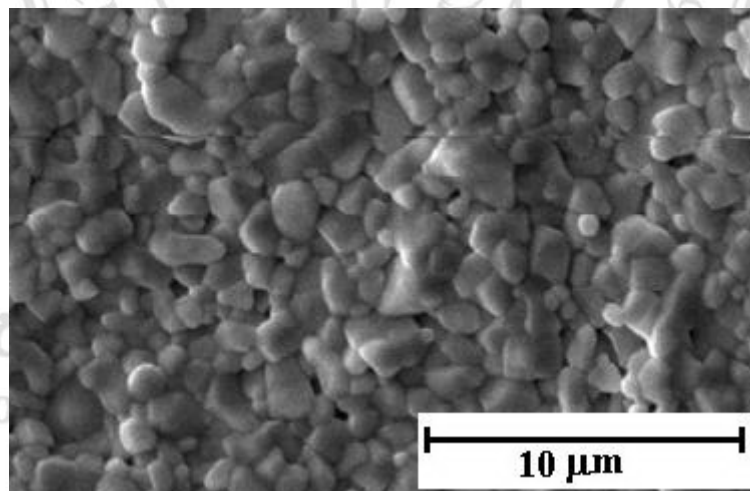


Figure 6.3 SEM micrographs of modified BFO ceramics with $x=0.005$.

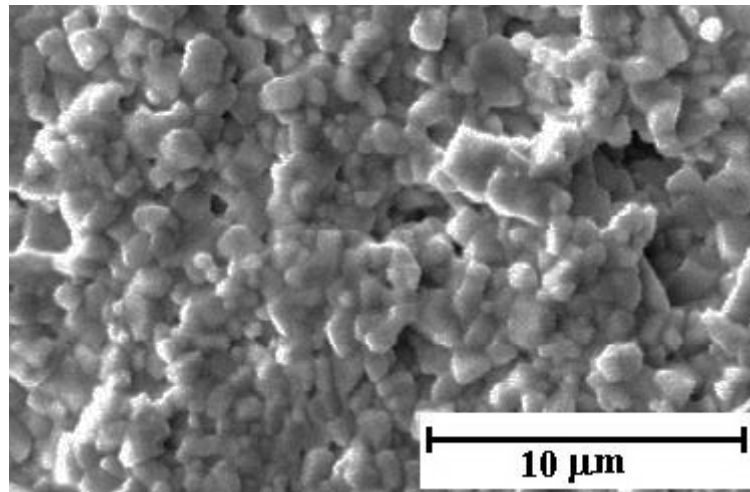


Figure 6.4 SEM micrographs of pure and modified BFO ceramics with $x=0.010$.

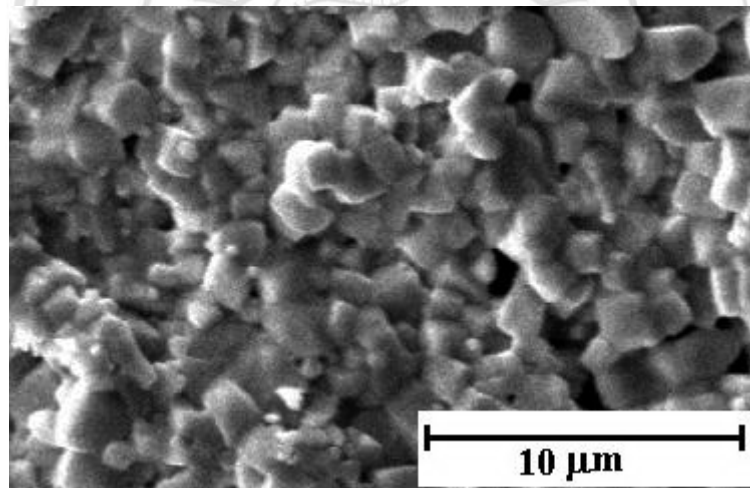


Figure 6.5 SEM micrographs of pure and modified BFO ceramics with $x=0.030$.

The SEM micrographs of the selected ceramic surfaces are illustrated in Fig. 6.2-6.5. It can be seen that small amount of Sb additive produces a large change in grain size. Average values of grain size, sharply decreases from $\sim 14 \mu\text{m}$ for the pure BFO ceramic to $\sim 3 \mu\text{m}$ for the $x = 0.005$ ceramic and then slightly changes with further Sb concentrations. This result suggests that Sb doping not only inhibits the BFO phase formation but also suppresses the grain growth. The impurity phases may be formed at the

grain boundaries and prevent grain boundary movement during the sintering process as a result in forming of fine grains in the modified samples.

TABLE 6.1. Energy band gap (E_g) and activation energy (E_a) of the studied ceramics.

Sb concentration (x)	E_g (eV)	E_a (eV)
0.000	2.5950	0.7520
0.005	2.5850	0.7718
0.010	2.5790	0.7908
0.030	2.5790	0.9412

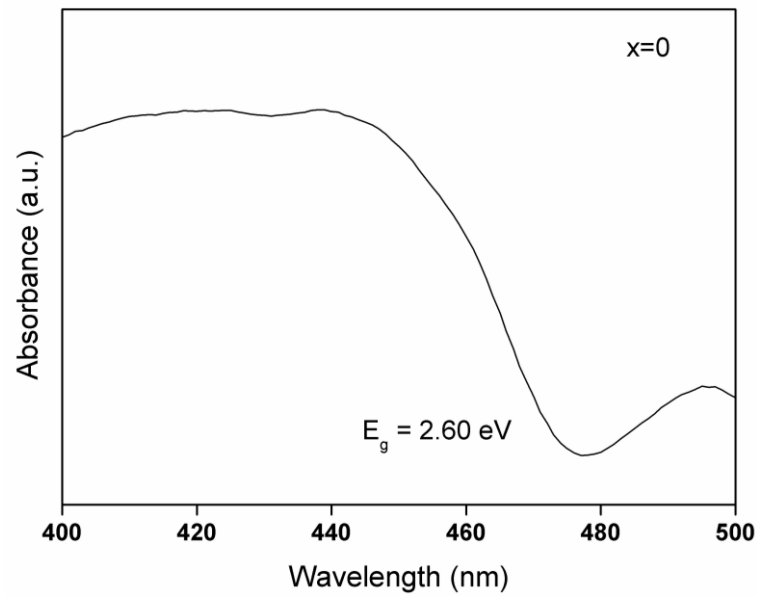


Figure 6.6 UV–Vis absorption spectrum of the BiFeO₃ when x=0.000.

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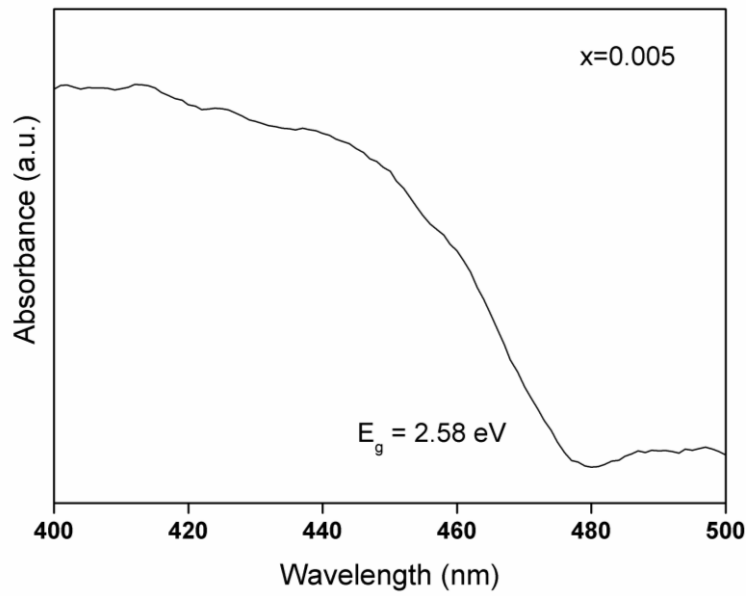


Figure 6.7 UV-Vis absorption spectrum of the BiFeO_3 when $x=0.005$.

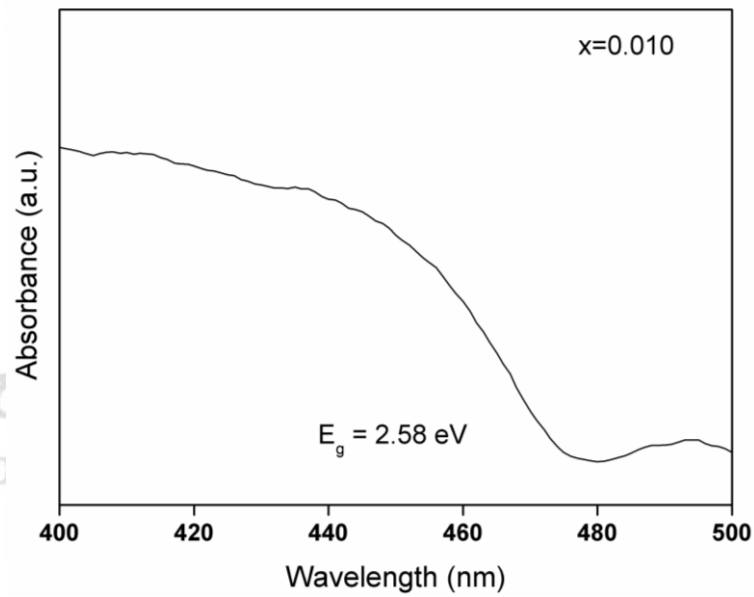


Figure 6.8 UV-Vis absorption spectrum of the BiFeO_3 when $x=0.010$.

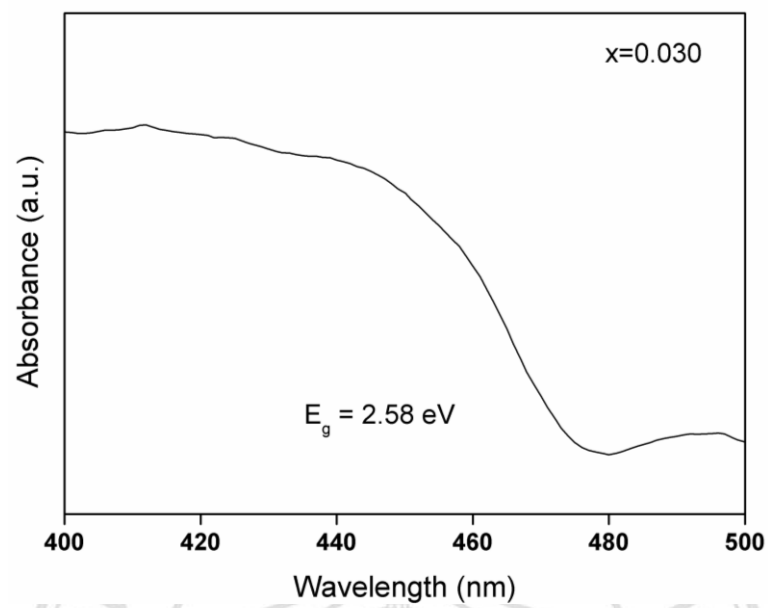


Figure 6.9 UV-Vis absorption spectrum of the BiFeO₃ when x=0.030.

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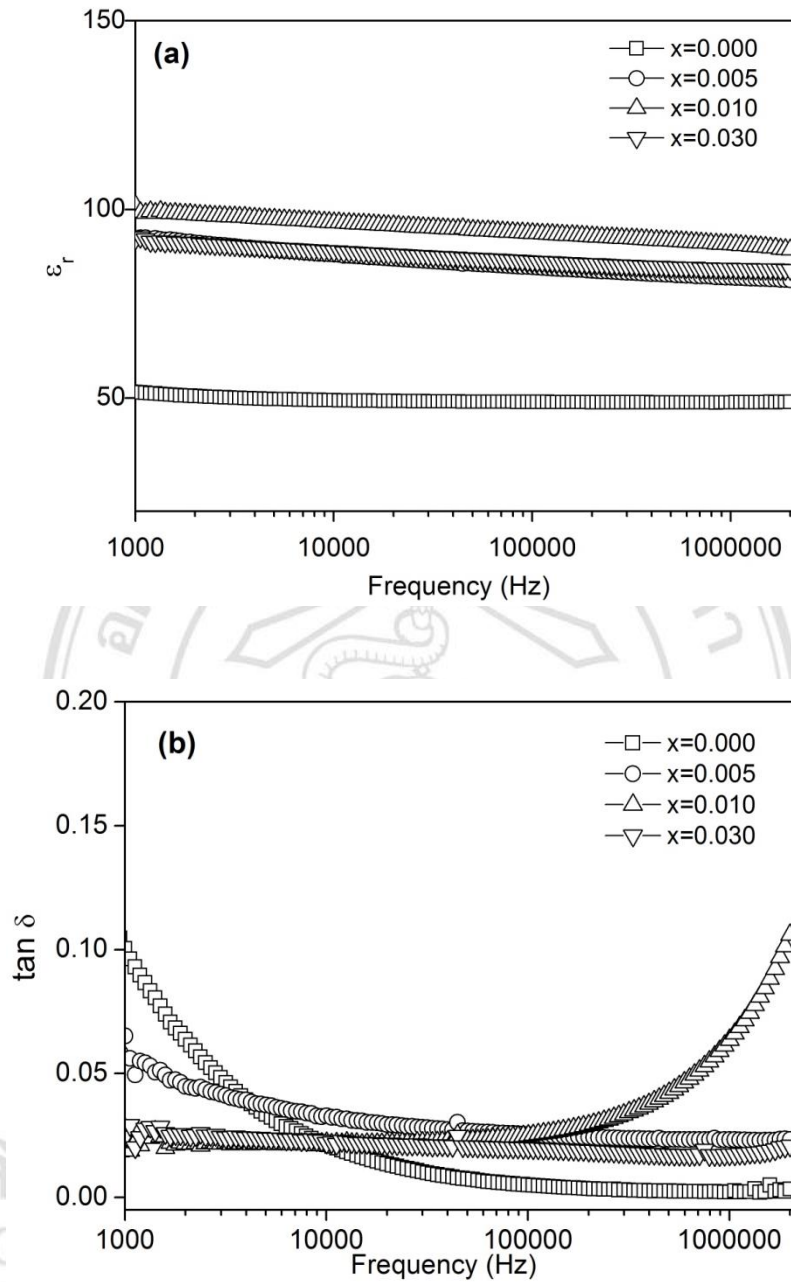


Figure 6.10 (a) Dielectric constant (ϵ_r) and (b) loss tangent ($\tan \delta$) as a function of frequency (at room temperature).

The dielectric constant and loss tangent as a function of frequency at room temperature is shown in Fig.6.10. General trend indicates that all samples exhibits a dielectric frequency stability, i.e. dielectric constant and loss tangent of all samples slightly change with increasing frequency. In case the pure BFO ceramics, the dielectric

constant at 10 kHz is ~ 50 . This value is consistent with many previous works [15]. After doping, an enhancement in dielectric constant is noted. The dielectric constants of modified ceramics are in a range of 88-97, but the 0.010 samples shows the maximum dielectric constant. In addition, the loss tangent values of all ceramics are lower than 0.04.

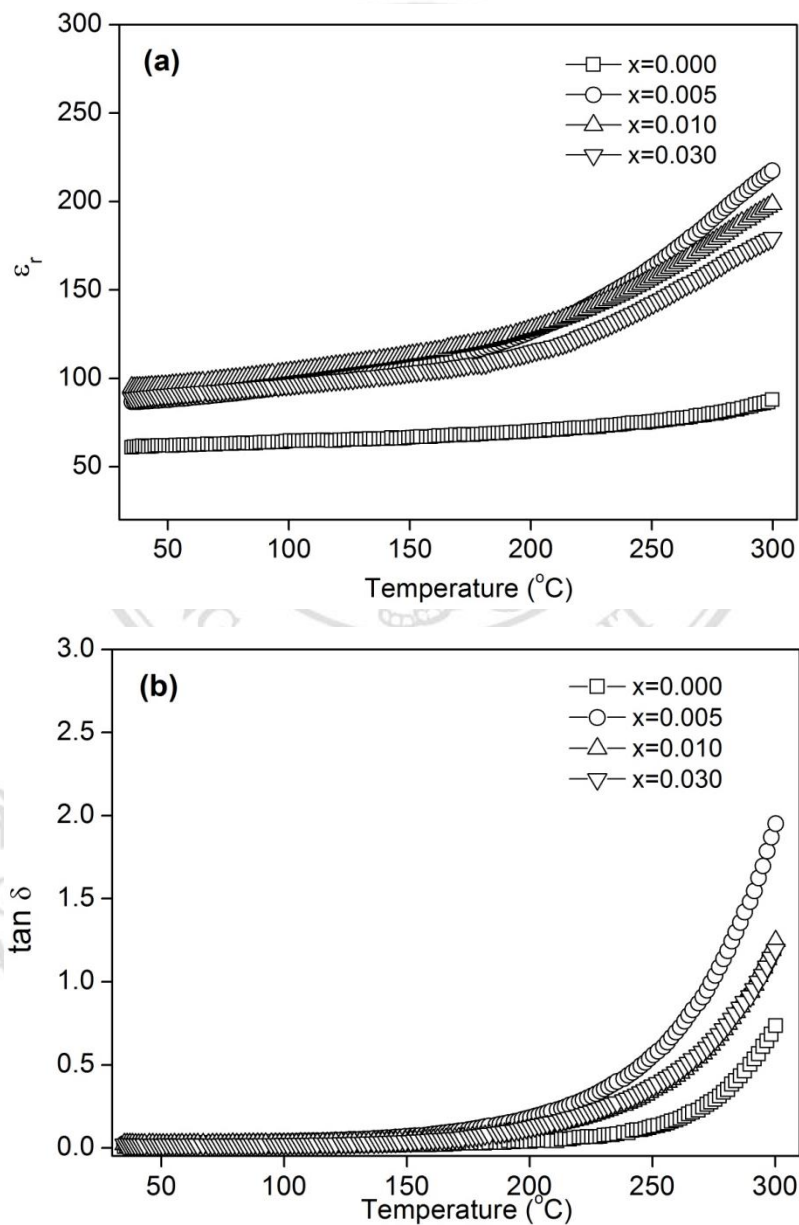


Figure 6.11 XRD patterns of BFO sintered ceramics.

The temperature dependence of the dielectric properties of the studied ceramics at 10 kHz is shown in the Fig.6.11. All samples presented an increase in dielectric constant and loss tangent with the temperature. The increase in dielectric constant and loss tangent with increasing temperature can be related to the thermally induced enhancement of the conductivity contribution [16]. It should be noted that Sb doping also produces an enhancement in the dielectric constant though the measured temperature.

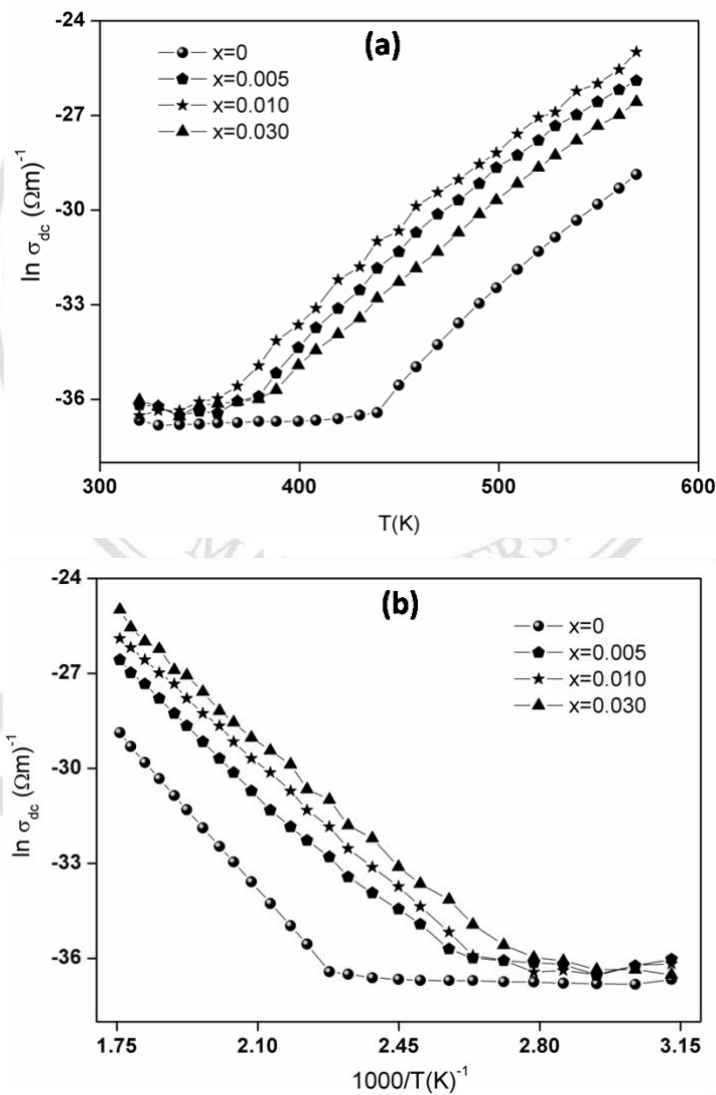


Figure 6.12 (a) dc-conductivity versus Temperature and (b) Arrhenius plots for the ceramics.

To check the conduction mechanism at high temperature. Conductivity (dc) as a function of temperature was performed. Fig.6.12(a) presents plots of dc conductivity versus temperature of the studied ceramics. The activation energy (E_a) was also calculated from this data by means of fitting an Arrhenius plots as seen in Fig.6.12(b). The activation energy values are in a range of 0.75-0.94 eV (Table 1). Therefore, conduction mechanism at high temperature can be related to oxygen vacancy conduction ($E_a=0.89$ eV).

To investigate the effect of Sb doping on the electrical properties in more detail, a technique of impedance spectroscopy was used in this work. Fig. 6.13 shows complex impedance planes measured at room temperature. In this work, all plots show only part of a semi-circle, with the centre lying below the Z' -axis. This character is similar to previous works [17-18] Therefore, a parallel combination of a resistor (R) and capacitor (C) is used to model conduction processes in this work [17-18]. The unmodified sample has bigger arc than that of the modified samples. This indicates a higher resistance the unmodified samples, i.e. the addition of Sb_2O_3 could reduce the resistivity of the modified ceramics. Thus, the enhancement in dielectric constant of the modified samples can be linked with conduction mechanism in the ceramics.

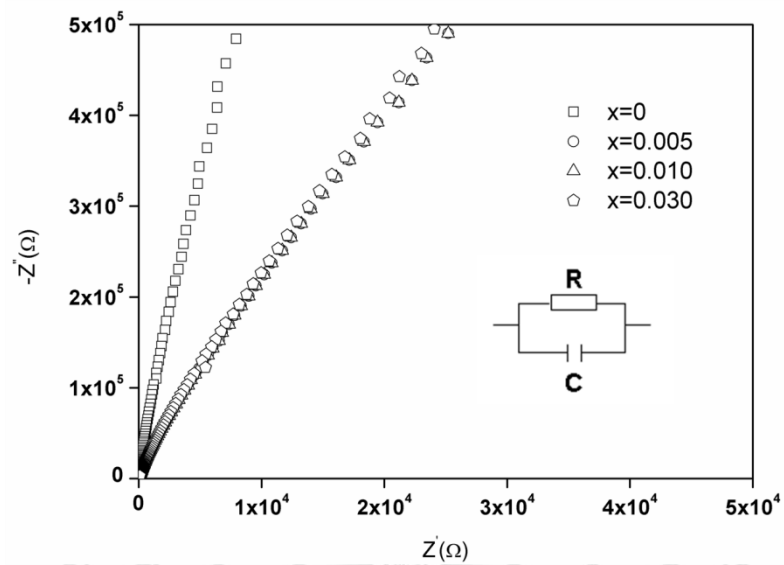


Figure 6.13 Nyquist plots of the impedance (Z' and Z'') the pure BFO and modified BFO ceramics. Inset show the equivalent circuit.

6.4 Conclusion

Phase formation, microstructure, and dielectric properties of the pure and Sb doped BFO ceramics were determined. Main phase of the studied ceramics is BFO. The obtained data also indicates that small amount of Sb ions have entered into the BFO lattices. A large change in grain size after doping, suggested that the additive suppresses grain growth. Addition of the additive also results the enhancement in dielectric constant which can be linked with oxygen vacancy conduction.

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6.5 Reference

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